

Qualified Levels: RoHS **NPN Darlington Power Silicon Transistor** JAN, JANTX, and Available on JANTXV commercial Qualified per MIL-PRF-19500/502 versions DESCRIPTION This high speed NPN transistor is rated at 12 amps and is military qualified up to a JANTXV level. This TO-204AA isolated package features a 180 degree lead orientation. Important: For the latest information, visit our website http://www.microsemi.com. **TO-204AA** (TO-3) **FEATURES** Package JEDEC registered 2N6058 and 2N6059 • JAN, JANTX, and JANTXV qualifications are available per MIL-PRF-19500/502 RoHS compliant versions available (commercial grade only) **APPLICATIONS / BENEFITS** Military, space and other high reliability applications High frequency response TO-204AA case with isolated terminals MAXIMUM RATINGS @ T_c = +25 °C unless otherwise noted **Parameters/Test Conditions** Symbol Value Unit °C Junction and Storage Temperature T_J and T_{STG} -55 to +175 MSC – Lawrence Thermal Resistance Junction-to-Case °C/W 1.0 R_{ejc} 6 Lake Street, Lawrence, MA 01841 **Collector Current** lc 12 А 1-800-446-1158 Collector-Emitter Voltage 2N6058 80 V VCEO (978) 620-2600 2N6059 100 Fax: (978) 689-0803 V Collector-Base Voltage 2N6058 V_{CBO} 80 2N6059 100 MSC – Ireland Gort Road Business Park, V Emitter-Base Voltage V_{EBO} 5 Ennis, Co. Clare, Ireland @ $T_c = +25 °C^{(1)}$ W **Total Power Dissipation** PΤ 150 Tel: +353 (0) 65 6840044 @ $T_{C} = +100 \,^{\circ}C$ 75 Fax: +353 (0) 65 6822298 Notes: 1. Derate linearly 1.0 W/°C above $T_c > +25$ °C. Website: www.microsemi.com



MECHANICAL and PACKAGING

- CASE: Industry standard TO-204AD (TO-3), hermetically sealed, 0.040 inch diameter pins.
- FINISH: Solder dipped tin-lead over nickel plated alloy 52 or RoHS compliant matte-tin plating. Solderable per MIL-STD-750 method 2026.
- POLARITY: NPN (see schematic)
- MOUNTING HARDWARE: Consult factory for optional insulator and sheet metal screws
- WEIGHT: Approximately 15 grams
- See package dimensions on last page.

PART NOMENCLATURE



	SYMBOLS & DEFINITIONS				
Symbol	Definition				
I _B	Base current: The value of the dc current into the base terminal.				
Ι _C	Collector current: The value of the dc current into the collector terminal.				
Ι _Ε	Emitter current: The value of the dc current into the emitter terminal.				
Τ _C	Case temperature: The temperature measured at a specified location on the case of a device.				
V _{CB}	Collector-base voltage: The dc voltage between the collector and the base.				
V _{CBO}	Collector-base voltage, base open: The voltage between the collector and base terminals when the emitter terminal is open-circuited.				
V _{CC}	Collector-supply voltage: The supply voltage applied to a circuit connected to the collector.				
V _{CE}	Collector-emitter voltage: The dc voltage between the collector and the emitter.				
V _{CEO}	Collector-emitter voltage, base open: The voltage between the collector and the emitter terminals when the base terminal is open-circuited.				
V _{EB}	Emitter-base voltage: The dc voltage between the emitter and the base.				
V _{EBO}	Emitter-base voltage, collector open: The voltage between the emitter and base terminals with the collector terminal open-circuited.				



ELECTRICAL CHARACTERISTICS $@T_A = +$	+25 °C unless otherwise noted
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Characteristics		Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage IC = 100 mA	2N6058 2N6059	V(BR)CEO	80 100		V
Collector-Emitter Cutoff Current VCE = 40 V VCE = 50 V	2N6058 2N6059	ICEO		1.0 1.0	mA
Collector-Emitter Cutoff Current VCE = 80 V, VEB = 1.5 V VCE = 150 V, VEB = 1.5 V	2N6058 2N6059	ICEX		10 10	μΑ
Emitter-Base Cutoff Current VEB = 5.0 V		IEBO		2.0	mA

ON CHARACTERISTICS

Forward-Current Transfer Ratio IC = 1.0 A, VCE = 3.0 V IC = 6.0 A, VCE = 3.0 V IC = 12 A, VCE = 3.0 V	hFE	1,000 1,000 150	18,000	
Collector-Emitter Saturation Voltage IC = 12 A, IB = 120 mA IC = 6.0 A, IB = 24 mA	VCE(sat)		3.0 2.0	V
Base-Emitter Saturation Voltage IC = 12 A, IB = 120 mA	VBE(sat)		4.0	V
Base-Emitter Voltage Non-saturated VCE = 3.0 V, IC = 6 A	VBE		2.8	V

DYNAMIC CHARACTERISTICS

Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio IC = 5 A, VCE = 3.0 V, f = 1 kHz	hfe	1,000		
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio IC = 5 A, VCE = 3.0 V, f = 1 MHz	h _{fe}	10	250	
Output Capacitance VCB = 10 V, IE = 0, f = 100 kHz \leq f \leq 1 MHz	Cobo		300	pF



ELECTRICAL CHARACTERISTICS @ $T_c = 25$ °C unless otherwise noted. (continued)

SWITCHING CHARACTERISTICS

Turn-On Time VCC = 30 V, IC = 5 A; IB1= 20 mA	t _{on}	2.0	μs
Turn-Off Time V _{CC} = 30 V, I _C = 5 A; I _{B1} = 20 mA	t _{off}	10	μs

SAFE OPERATING AREA (See figures 1 and 2 and MIL-STD-750, Test Method 3053)

DC Tests TC = +25 °C, +10 °C, -0 °C, t ≥ 1 second, 1 Cycle Test 1 VCE = 12.5 V, IC = 12 A Test 2 VCE = 30 V, IC = 5 A Test 3 VCE = 70 V, IC = 200 mA (2N6058) VCE = 90 V, IC = 155 mA (2N6059)



SAFE OPERATING AREA



Maximum Safe Operating Area (continuous dc)



SAFE OPERATING AREA (continued)



(unclamped inductive load)



PACKAGE DIMENSIONS



Ltr	Inches		Millimeters		Notes	
	Min	Max	Min Max			
CD	-	0.875	-	22.23		
СН	0.250	0.328	6.35	8.33		
HR	0.495	0.525	12.57	13.34		
HR1	0.131	0.188	3.33	4.78	3	
HT	0.060	0.135	1.52	3.43		
LD	0.038	0.043	0.97	1.09	4, 5	
LL	0.312	0.500	7.92	12.70	4	
LL1	-	0.050	-	1.27	4, 5	
MHD	0.151	0.161	3.84	4.09	6	
MHS	1.177	1.197	29.90	30.40		
PS	0.420	0.440	10.67	11.18	7, 8	
PS1	0.205	0.225	5.21	5.72	7, 4, 8	
S1	0.655	0.675	16.64	17.15	7	
T1	Emitter					
T2	Base					
Case	Collector					

NOTES:

- 1. Dimensions are in inches. Millimeters are given for information only.
- 2. Body contour is optional within zone defined by dimension CD.
- 3. At both ends
- 4. Both terminals
- 5. Dimension LD applies between dimension L1 and LL. Lead diameter shall not exceed twice dimension LD within dimension L1. Diameter is uncontrolled in dimension L1.
- 6. Two holes
- 7. These dimensions shall be measured at points 0.050 inch (1.27 mm) to 0.055 inch (1.40 mm) below the seating plane. When gauge is not used, measurement shall be made at seating plane.
- 8. The seating plane of the header shall be flat within 0.001 inch (0.03 mm) concave to 0.004 inch (0.10 mm) convex inside a 0.930 inch (23.62 mm) diameter circle on the center of the header and flat within 0.001 inch (0.03 mm) concave to 0.006 inch (0.15 mm) convex overall.
- 9. The collector shall be electrically connected to the case.
- 10. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.

See schematic on next page



SCHEMATIC

